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TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

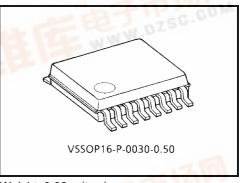
TC7MZ4051FK,TC7MZ4052FK,TC7MZ4053FK

TC7MZ4051FK 8-Channel Analog Multiplexer/Demultiplexer TC7MZ4052FK Dual 4-Channel Analog Multiplexer/Demultiplexer TC7MZ4053FK Triple 2-Channel Analog Multiplexer/Demultiplexer

The TC7MZ4051/4052/4053FK are high-speed, low-voltage drive analog multiplexer/demultiplexers using silicon gate CMOS technology. In 3 V and 5 V systems these can achieve high-speed operation with the low power dissipation that is a feature of CMOS.

The TC7MZ4051/4052/4053FK offer analog/digital signal selection as well as mixed signals. The 4051 has an 8-channel configuration, the 4052 has an 4-channel × 2 configuration, and the 4053 has a 2-channel × 3 configuration.

The switches for each channel are turned ON by the control pin digital signals.



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Weight: 0.02 g (typ.)

Although the control signal logical amplitude ($V_{CC} - GND$) is small, the device can perform large-amplitude ($V_{CC} - V_{EE}$) signal switching.

For example, if $V_{CC} = 3 \text{ V}$, GND = 0 V, and $V_{EE} = -3 \text{ V}$, signals between -3 V and +3 V can be switched from the logical circuit using a single 3 V power supply.

All input pins are equipped with a newly developed input protection circuit that avoids the need for a diode on the plus side (forward side from the input to the V_{CC}). As a result, for example, 5 V signals can be permitted on the inputs even when the power supply voltage to the circuits is off. As a result of this input power protection, the TC7MZ4051/4052/4053FK can be used in a variety of applications, including in the system which has two power supplies, and in battery backup circuits.

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Features

• Low ON resistance: $R_{on} = 22 \Omega (typ.) (V_{CC} - V_{EE} = 3 V)$

$$R_{on} = 15 \Omega$$
 (typ.) (V_{CC} - V_{EE} = 6 V

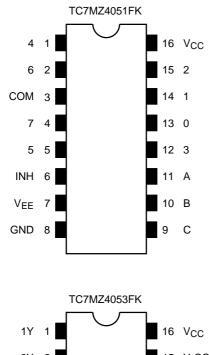
- High speed: $t_{pd} = 3 \text{ ns} (typ.) (V_{CC} = 3.0 \text{ V})$
- Low power dissipation: $I_{CC} = 4 \mu A (max) (Ta = 25^{\circ}C)$
- Input level: $V_{IL} = 0.8 V (max) (V_{CC} = 3 V)$

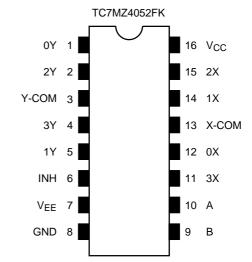
$$V_{IH} = 2.0 V (min) (V_{CC} = 3 V)$$

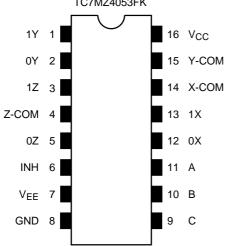
- Power down protection is provided on all control inputs
- Pin and function compatible with 74HC4051/4052/4053

TC7MZ4051,4052,4053FK

Pin Assignment (top view)







Truth Table

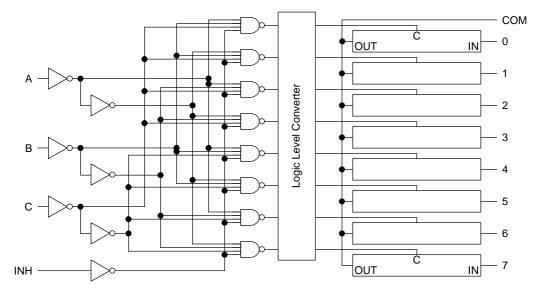
	Contro	I Inputs		"ON" Channel				
Inhibit	C*	В	А	MZ4051FK	MZ4052FK	MZ4053FK		
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z		
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z		
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z		
L	L	Н	Н	3	3X, 3Y	1X, 1Y, 0Z		
L	Н	L	L	4	—	0X, 0Y, 1Z		
L	н	L	Н	5	—	1X, 0Y, 1Z		
L	н	Н	L	6	—	0X, 1Y, 1Z		
L	Н	Н	Н	7	—	1X, 1Y, 1Z		
Н	Х	Х	Х	None	None	None		

X: Don't care, *: Except MZ4052FK

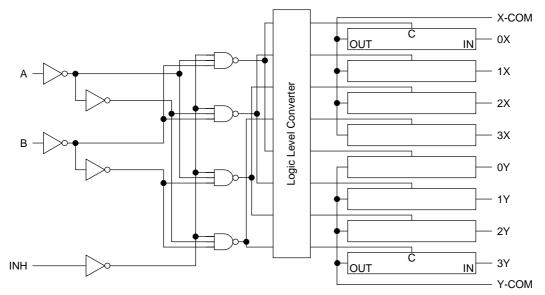
TC7MZ4051,4052,4053FK

System Diagram

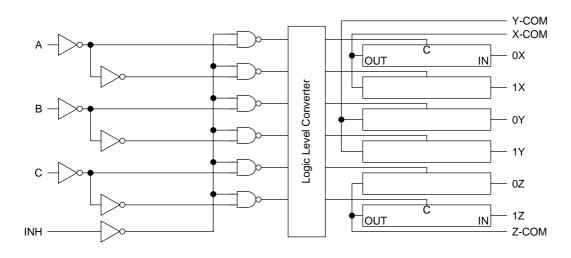
TC7MZ4051FK



TC7MZ4052FK



TC7MZ4053FK



TC7MZ4051,4052,4053FK

Absolute Maximum Ratings

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~7.0	v	
Fower supply voltage	V _{CC} ~V _{EE}	-0.5~7.0		
Control input voltage	V _{IN}	-0.5~7.0	V	
Switch I/O voltage	V _{I/O}	$V_{\text{EE}} - 0.5\text{-}V_{\text{CC}} + 0.5$	V	
Input diode current	I _{IK}	-20	mA	
I/O diode current	I _{IOK}	±20	mA	
Switch through current	Ι _Τ	±25	mA	
DC V_{CC} or ground current	ICC	±50	mA	
Power dissipation	PD	180	mW	
Storage temperature	T _{stg}	-65~150	°C	

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
	V _{CC}	2~6	
Power supply voltage	VEE	-4~0	V
	$V_{CC} \sim V_{EE}$	2~6	
Input voltage	V _{IN}	0~6.0	V
Switch I/O voltage	V _{I/O}	V _{EE} ~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~100 (V_{CC} = 3.3 \pm 0.3 V)	ns/V
	u.uv	0~20 (V _{CC} = 5 \pm 0.5 V)	115/ V

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Electrical Characteristics

DC Electrical Characteristics

Characteristics		Symbol Test Condition				-	Ta = 25°C			Ta = -40~85°C	
		Symbol	Test Condition	V_{EE} (V)	$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Unit
					2.0	1.5			1.5		
	High-level	VIH			3.0	2.0		_	2.0		
	i ligii-level	VIH			4.5	3.15	_	_	3.15	_	
Input voltage					6.0	4.2	_	_	4.2	_	V
mput voltage					2.0		_	0.5		0.5	v
	Low-level	VIL			3.0		_	0.8	_	0.8	
	LOW-IEVEI	۷IL	_		4.5			1.35	_	1.35	
					6.0			1.8		1.8	
			V _{IN} = V _{IL} or V _{IH}	GND	2.0		200			_	
			$V_{I/O} = V_{CC}$ to V_{EE}	GND	3.0		45	86		108	Ω
		R _{ON} –	$I_{I/O} = 2 \text{ mA}$	GND	4.5		24	37		46	
ON resistance				-3.0	3.0		17	26		33	
ONTESIStance			$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{I/O} = V_{CC} \text{ or } V_{EE}$ $I_{I/O} = 2 \text{ mA}$	GND	2.0		28	73	_	84	
				GND	3.0		22	38	_	44	
				GND	4.5		17	27	_	31	
				-3.0	3.0		15	24	_	28	
			$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{I/O} = V_{CC} \text{ to } V_{EE}$ $I_{I/O} = 2 \text{ mA}$	GND	2.0		10	25	—	35	Ω
Difference of O resistance betw		ΔR_{ON}		GND	3.0		5	15		20	
switches	Cen	ARON		GND	4.5		5	13		18	
			1/0 - 2 11/1	-3.0	3.0		5	10		15	
Input/Output lea	akade		$V_{OS} = V_{CC} \text{ or } GND$	GND	3.0			±0.25		±2.5	
(switch OFF)		I _{OFF}	$V_{IS} = GND \text{ to } V_{CC}$ $V_{IN} = V_{IL} \text{ or } V_{IH}$	-3.0	3.0		_	±0.5	_	±5.0	μΑ
Input/Output leakage current (switch ON, output open)			$V_{OS} = V_{CC}$ or GND	GND	3.0	_		±0.25	_	±2.5	
		I _{IN}	$V_{IN} = V_{IL} \text{ or } V_{IH}$	-3.0	3.0	_	_	±0.5	_	±5.0	μA
Control input current		I _{IN}	$V_{IN} = V_{CC}$ or GND	GND	6.0	_		±0.1		±0.1	μA
Quieseet au	by ourrest			GND	3.0	_	—	4.0	_	40.0	
Quiescent supp	ny current	ICC	$V_{IN} = V_{CC}$ or GND	-3.0	3.0			8.0	_	80.0	μΑ

AC Electrical Characteristics ($C_L = 50 \text{ pF}$, Input: $t_r = t_f = 3 \text{ ns}$, GND = 0 V)

Characteristics	Symbol	Test Condition					Ta = 25°C			Ta = -40~85°C	
Characteristics	Symbol			$V_{EE}(V)$	$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Unit
		All types		GND	2.0	_	3.2	6.0		6.9	ns
Phase difference between	φI/O			GND	3.0		1.8	3.0		3.5	
input and output	ψι/Ο			GND	4.5	_	1.3	1.8	_	2.1	115
				-3.0	3.0	—	1.1	1.3	_	1.5	
				GND	2.0	—	9.0	17	_	20	
Output enable time	t _{pZL}	Figure	1 (Note 1)	GND	3.0	_	5.7	9.0	_	11	00
	t _{pZH}	rigule		GND	4.5	—	4.5	6.0	_	7.0	ns
				-3.0	3.0	—	5.8	8.0	_	10	
Output disable time				GND	2.0	—	13.5	21		25	-
	t _{pLZ}	Figure 1 (N	1 (Note 1)	GND	3.0	—	11.3	15		18	
	t _p HZ			GND	4.5	_	10.3	12	_	14	ns
				-3.0	3.0	_	10.9	13	_	15	
Control input capacitance	C _{in}	All type	es (Note 2)	_	_	_	5	10	_	10	pF
		4051	Einung O		3.0	_	11	25		25	pF
COMMON terminal capacitance	C _{IS}	4052	Figure 2 (Note 2)	-3.0 3.0			9	20	—	20	
		4053				7	15	15	15	1	
		4051	Figure 2				6	13		13	
SWITCH terminal capacitance	C _{OS}	4052	(Note 2)	-3.0	3.0	—	6	13		13	pF
		4053					6	13		13	
		4051			3.0		3	6		6	
Feedthrough capacitance	CIOS	4052	Figure 2 (Note 2)	-3.0		_	3	6	—	6	pF
		4053	(1010 2)				3	6		6	
		4051				_	14				
Power dissipation capacitance	C _{PD}	4052	Figure 2 (Note 3)	GND	6.0		24	—		—	pF
		4053					18				

Note1: $R_L = 1 \ k\Omega$

Note2: C_{in}, C_{IS}, C_{OS} and C_{IOS} are guaranteed by the design.

Note3: CPD is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

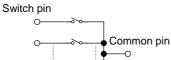
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

TC7MZ4051,4052,4053FK

*Analog Switch Characteristics (GND = 0 V, Ta = 25°C)

Characteristics	Symbol	Test Condition			Typ	Unit	
Characteristics	Symbol	Test Condition		V _{EE} (V)	V _{CC} (V)	тур.	Offic
			$V_{IN} = 2.0 V_{p-p}$	0	3.0	0.100	
Sine Wave Distortion (T.H.D)		$R_L = 10 k\Omega$, $C_L = 50 pF$, $f_{IN} = 1 kHz$	$V_{IN} = 4.0 V_{p-p}$	0	4.5	0.030	%
			$V_{IN} = 6.0 V_{p-p}$	-0.3	3.0		
			4051			150	MHz
			4052	0	3.0	180	
		Adjust f _{IN} voltage to obtain 0dBm at V _{OS} .	4053			200	
F		Increase f _{IN} frequency until dB	4051			150	
Frequency response	f _{max}	meter reads -3dB.	4052	0	4.5	180	
(switch ON)		$R_L = 50 \Omega$, $C_L = 10 pF$, $f_{IN} = 1 MHz$, sine wave	4053			200	
		Figure 3	4051		3.0	150	
			4052	-3.0		180	
			4053			200	
		V_{IN} is centered at $(V_{CC} - V_{EE})/2$.	0	3.0	-45	dB	
		Adjust input for 0dBm.	0		45		
		$R_L = 600 \ \Omega, \ C_L = 50 \ pF, \ f_{IN} = 1 \ M$	0	4.5	-45		
Feed through attenuation (switch OFF)		Figure 4	-3.0	3.0	-45		
(,			0	3.0	-60		
		$R_L = 50 \ \Omega$, $C_L = 10 \ pF$, $f_{IN} = 1 \ MHz$, sine wave		0	4.5	-60	
			-3.0	3.0	-60	l	
Crosstalk		$R_L = 600 \ \Omega$, $C_L = 50 \ pF$, $f_{IN} = 1 \ M$	Hz, square wave	0	3.0	90	
(control input to signal		$(t_r = t_f = 6 \text{ ns})$			4.5	150	mV
output)		Figure 5		-3.0	3.0	120	
Croostally		Adjust V _{IN} to obtain 0dBm at input	0	3.0	-45		
Crosstalk		$R_L=600~\Omega,~C_L=50~pF,~f_{IN}=1~M$	0	4.5	-45	dB	
(between any switches)	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	-45					

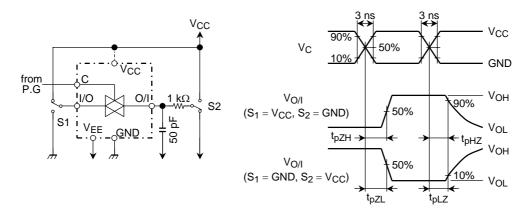
*: These characteristics are determined by design of devices.

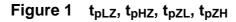


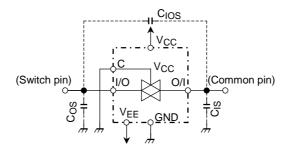
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AC Test Circuit









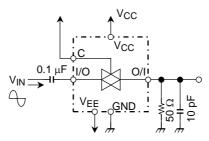


Figure 3 Frequency Response (switch on)

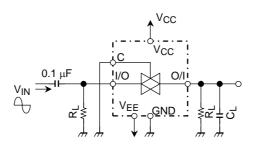
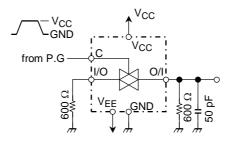


Figure 4 Feedthrough





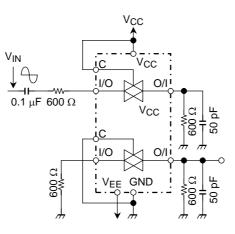


Figure 6 Cross Talk (between any two switches)

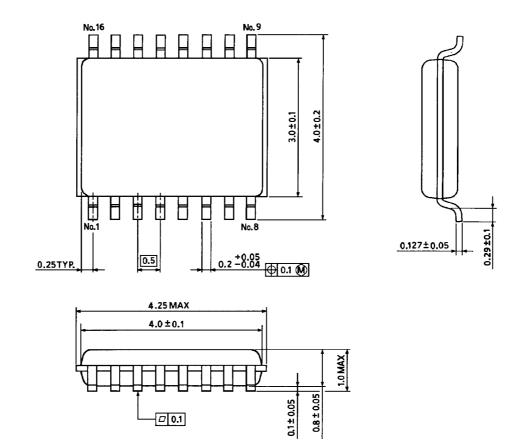
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TC7MZ4051,4052,4053FK

Package Dimensions

VSSOP16-P-0030-0.50

Unit : mm



Weight: 0.02 g (typ.)

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